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## Radiation damage in silicon photomultipliers exposed to neutron radiation

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### Content

We report on the measurement of the radiation hardness of newly developed silicon photomultipliers (SiPMs) manufactured by Hamamatsu Corporation (Japan). The SiPMs were irradiated with neutrons up to 1 MeV equivalent fluence of  $2 * 10^{12} n/cm^2$  at TRIGA Marc II research reactor in Ljubljana. The SiPM's main parameters were measured before and after irradiation. The effects of the radiation on many parameters such as gain, intrinsic dark current, photon detection efficiency and noise for these devices are shown and discussed.

### Summary

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